

# **PMV65XPEA** 20 V, P-channel Trench MOSFET

27 November 2014

**Product data sheet** 

# 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Very fast switching
- Enhanced power dissipation capability: Ptot = 890 mW
- ElectroStatic Discharge (ESD) protection 2 kV HBM
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High speed line driver
- High-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	-	-3.3	А
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -2.8 A; T <sub>j</sub> = 25 °C		-	67	78	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

# nexperia

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G G S 017aaa259

# 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PMV65XPEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMV65XPEA	DN%

[1] % = placeholder for manufacturing site code

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

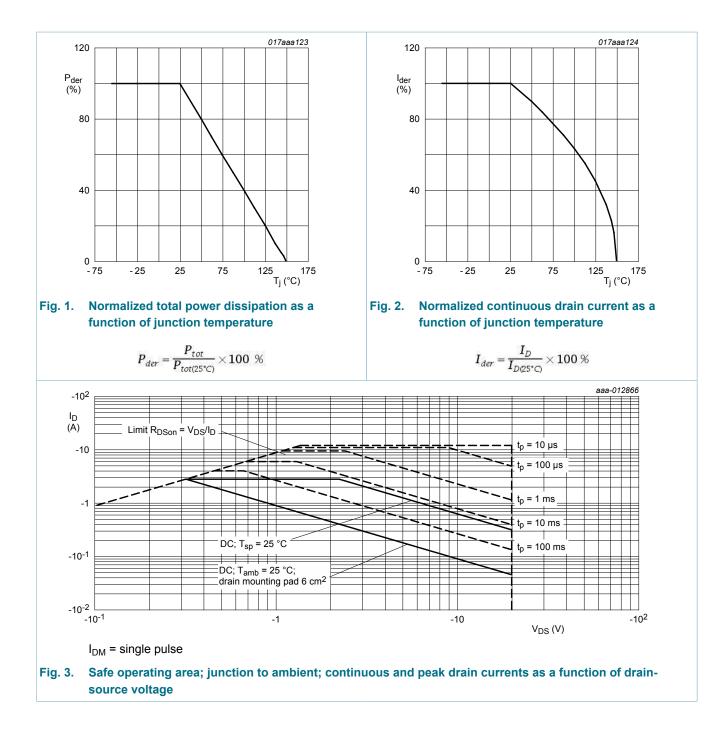
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-3.3	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-2.8	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-1.8	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-12	А
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = -0.52 A; DUT in avalanche (unclamped)		-	5.4	mJ
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	480	mW
			[1]	-	890	mW
		T <sub>sp</sub> = 25 °C		-	6250	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode	·				
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-0.9	А
ESD maxim	num rating	1				
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

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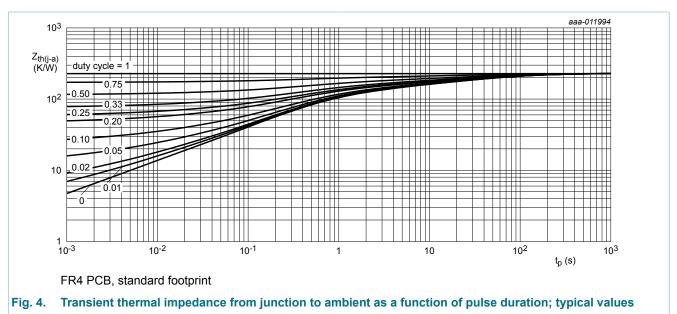


#### **Thermal characteristics** 9.

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	230	260	K/W
			[2]	-	120	140	K/W
		in free air; $t \le 5 s$	[2]	-	85	100	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	15	20	K/W

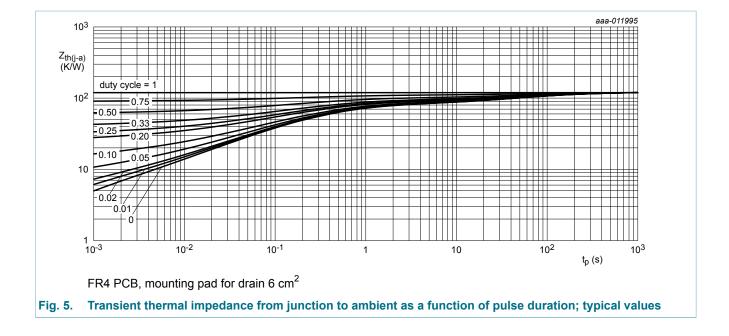
Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [1] [2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



# **PMV65XPEA**

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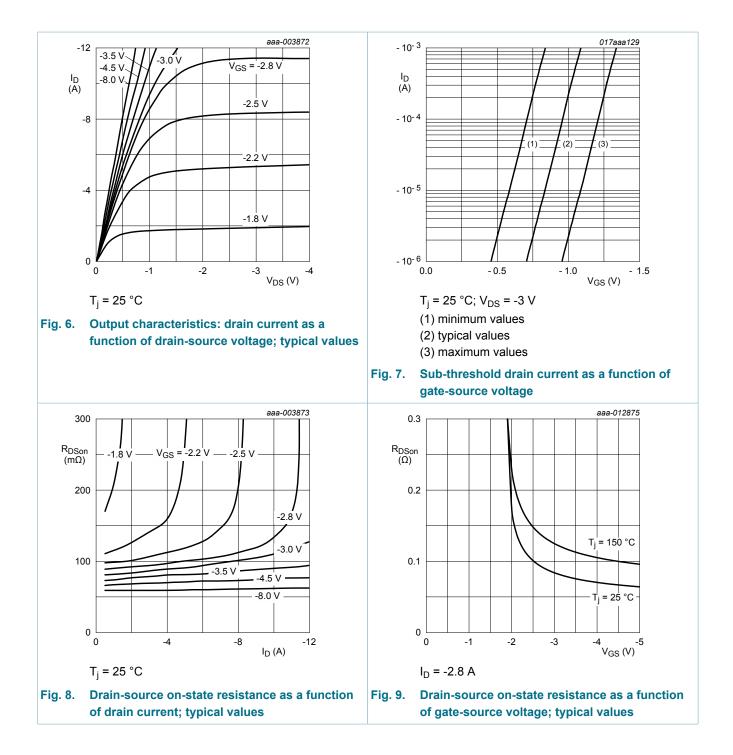


# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = -250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.75	-1	-1.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		$V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	2	μA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-2	μA
20011	drain-source on-state	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -2.8 A; T <sub>j</sub> = 25 °C	-	67	78	mΩ
resist	resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -2.8 A; T <sub>j</sub> = 150 °C	-	98	114	mΩ
		$V_{GS}$ = -2.5 V; I <sub>D</sub> = -2.2 A; T <sub>j</sub> = 25 °C	-	99	125	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -2 A; T <sub>j</sub> = 25 °C	-	7.4	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	11.6	-	Ω
Dynamic ch	aracteristics	· · · · ·				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; I <sub>D</sub> = -2.8 A; V <sub>GS</sub> = -4.5 V;	-	5	9	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	1.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	618	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	80	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	58	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; I <sub>D</sub> = -2.8 A; V <sub>GS</sub> = -4.5 V;	-	7	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	19	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	36	-	ns
t <sub>f</sub>	fall time		-	17	-	ns
Source-drai	n diode	1			1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -0.85 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.75	-1.2	V

# **PMV65XPEA**

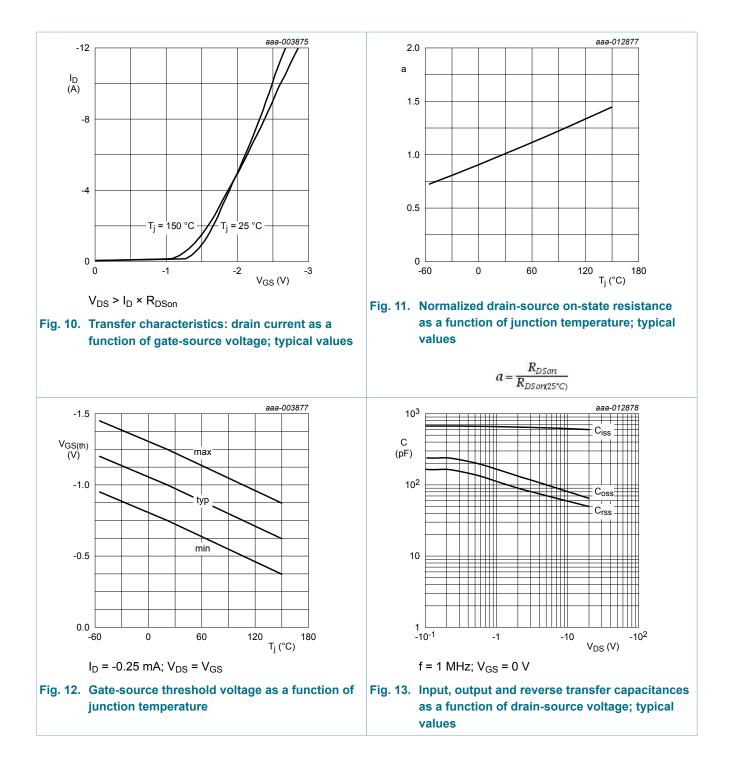
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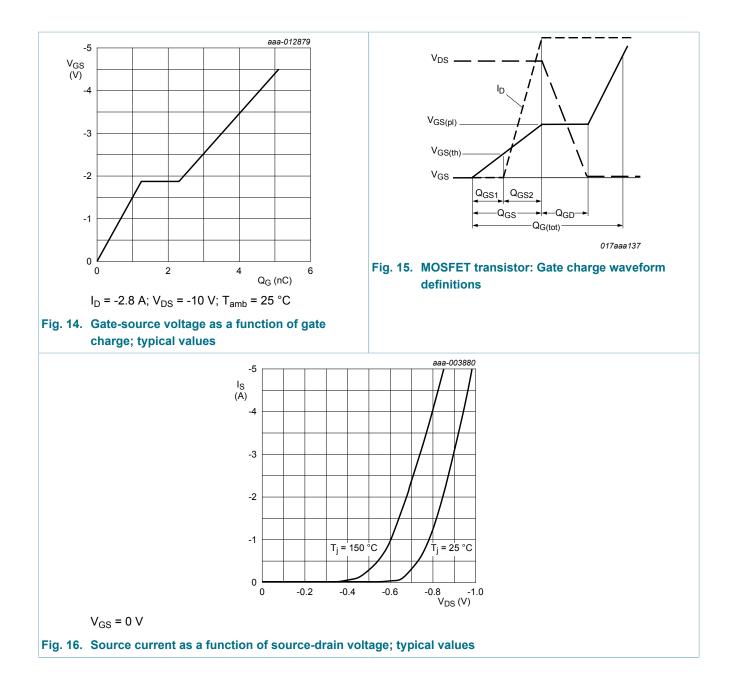
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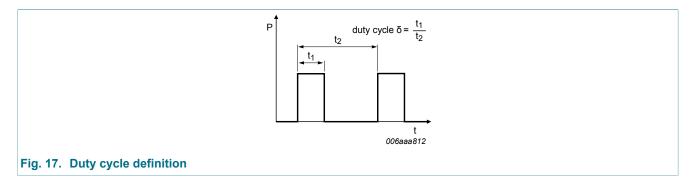


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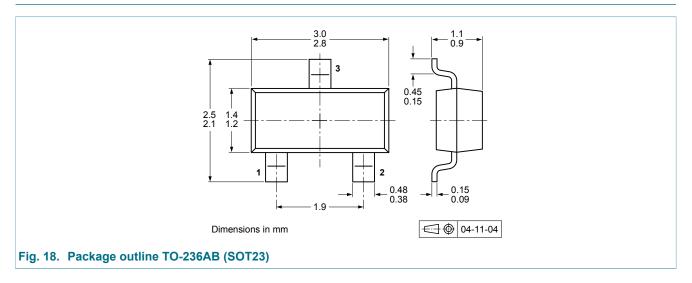
# **11. Test information**



#### **11.1 Quality information**

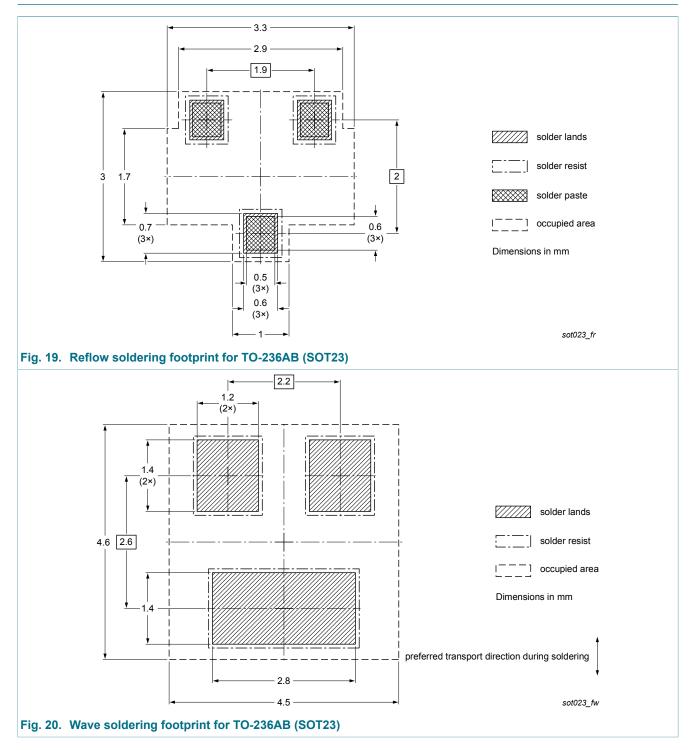
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

### 12. Package outline



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# 13. Soldering



# 14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMV65XPEA v.1	20141127	Product data sheet	-	-			

#### 20 V, P-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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